

LNA2606L

GaAlAs on GaAs Infrared Light Emitting Diode

For optical control systems

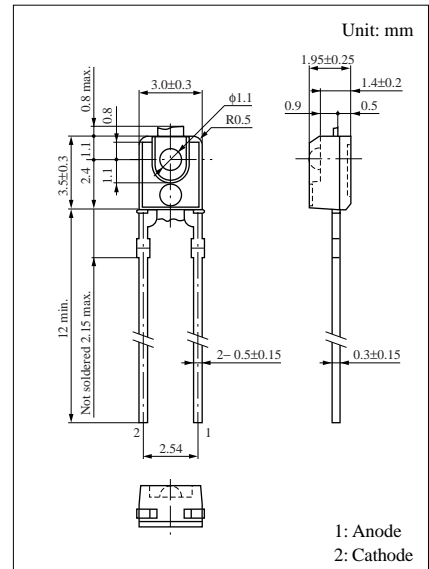
■ Features

- High-power output, high-efficiency: $P_O = 9 \text{ mW min.}$
- Emitted light spectrum suited for silicon photodetectors
- Ultra-miniature, thin side-view type package
- Long lifetime, high reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Power dissipation	P_D	80	mW
Forward current (DC)	I_F	50	mA
Pulse forward current *	I_{FP}	1	A
Reverse voltage (DC)	V_R	3	V
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +100	$^\circ\text{C}$

Note) *: $f = 100 \text{ Hz}$, Duty Cycle = 0.1%



■ Electro-Optical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	P_O	$I_F = 50 \text{ mA}$	9		19	mW
Peak emission wavelength	λ_p	$I_F = 50 \text{ mA}$		940		nm
Spectral half band width	$\Delta\lambda$	$I_F = 50 \text{ mA}$		50		nm
Forward voltage (DC)	V_F	$I_F = 50 \text{ mA}$		1.3	1.6	V
Reverse current (DC)	I_R	$V_R = 3 \text{ V}$			10	μA
Capacitance between pins	C_t	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$		35		pF
Half-power angle	θ	The angle in which radiant intensity is 50%		20		$^\circ$